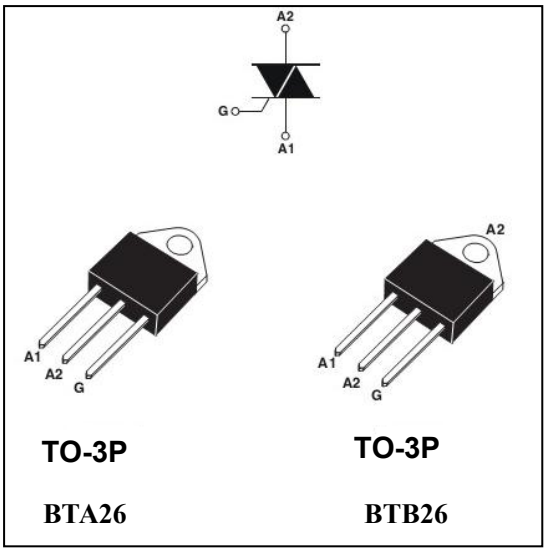
26A 4Quadrants TRIACs

Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	26	A
V_{DRM} V_{RRM}	800/1000	V
V_{TM}	1.50	V



Features

With high ability to withstand the shock loading of arge current, Provide high dv/dt rate with strong resistance to electromagnetic interference

Application

Power charger, T-tools, massager, solid staterelay, AC Motor speed regulation and so on.

Order Information

Part Number	Package	Marking	Packing	Packing Quantity
BTA26-800B	TO-3P	BTA26-800B XXXX	box	600PCS/box
BTA26-1000B	TO-3P	BTA26-1000BXXXX	box	600PCS/box
BTB26-800B	TO-3P	BTB26-800B XXXX	box	600PCS/box
BTB26-1000B	TO-3P	BTB26-1000BXXXX	box	600PCS/box

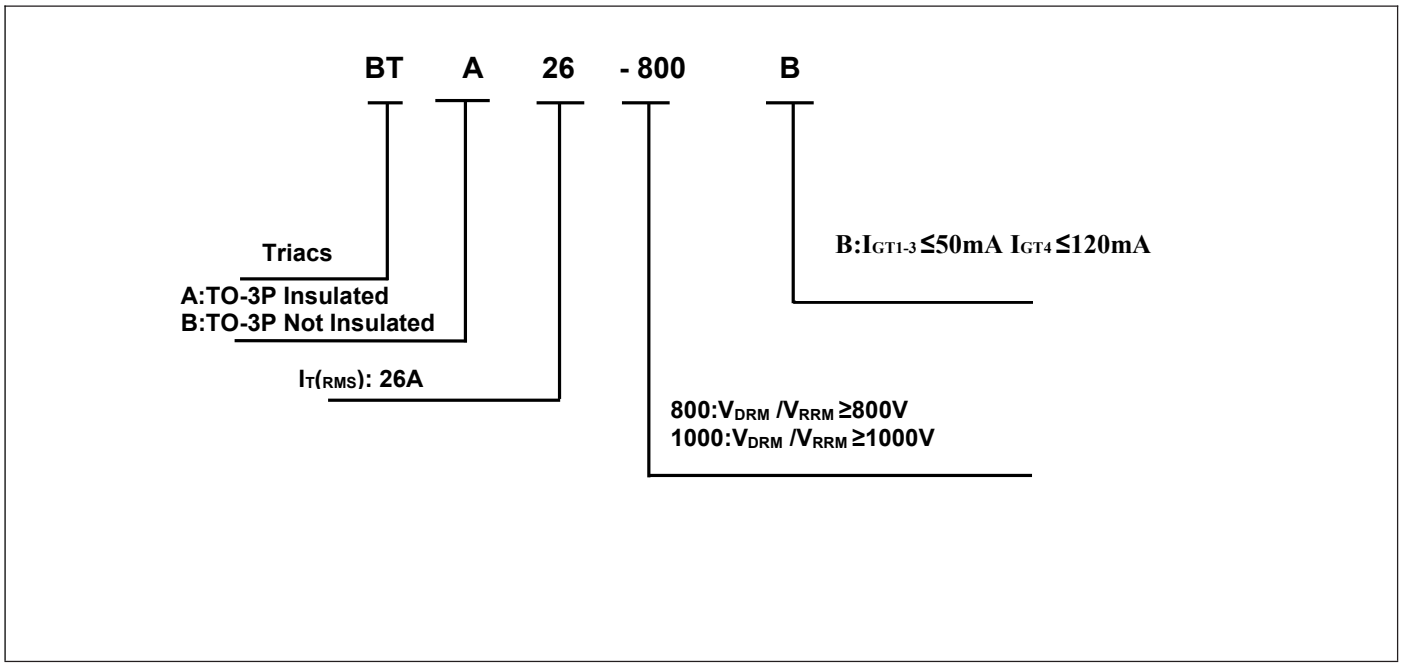
Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Repetitive peak off-state voltage	**V_{DRM}**	800/1000	**V**
Repetitive peak reverse voltage	**V_{RRM}**	800/1000	**V**
RMS on-state current（BTA Tc=80℃，BTB Tc=90℃）	$I_{T(RMS)}$	26	A
Non repetitive surge peak on-state current (t=20ms, F=50Hz)	I_{TSM}	260	A
I^2t value for fusing (tp=10ms)	I^2t	340	A^2S
Critical rate of rise of on-state current（Tj=125℃）	dI/dt	50	A/μs
Peak gate current（tp=20us，Tj=125℃）	I_{GM}	4	A
Average gate power dissipation（Tj=125℃）	$P_{G（AV）}$	1	W
Junction Temperature	T_J	-40-+125	°C
Storage Temperature	T_{STG}	-40 ~+150	°C

Electrical characteristics (T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition		Value		Unit
Gate trigger current	I_{GT}	V_D=12V R_L=100Ω	Ⅰ-Ⅱ-Ⅲ	MAX.	≤50	mA
			Ⅳ	MAX.	≤120	mA
Gate trigger voltage	V_{GT}		-	MAX.	1.5	**V**
Gate non-trigger voltage	V_{GD}	V_D=V_{DRM} T_j=125°C	Ⅰ-Ⅱ-Ⅲ	MIN.	0.2	**V**
Holding current	I_H	I_T=0.5A	-	MAX.	60	**mA**
latching current	I_L	lG=1.2lGT	-	MAX.	60	**mA**
			-	MAX.	100	**mA**
Critical-rate of rise of commutation voltage	**dV/dt**	V_D=2/3V_{DRM} Tj=125°C		MIN.	500	**V/μs**
STATIC CHARACTERISTICS						
Forward "on" voltage	V_{TM}	I_{TM}= 52A		MAX.	1.50	**V**
Repetitive Peak Off-State Current	I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25°C	MAX.	10	**μA**
Repetitive Peak Reverse Current	I_{RRM}		T_j=125°C	MAX.	2	**mA**
THERMAL RESISTANCES						
Thermal resistance	**Rth(j-c)**	Junction to case		BTA	0.9	**°C/W**
	Rth(j-a)	Junction to ambient		BTB	0.6	**°C/W**

Ordering Information



Typical Characteristics

FIG1

Maximum power dissipation versus RMS on-state current

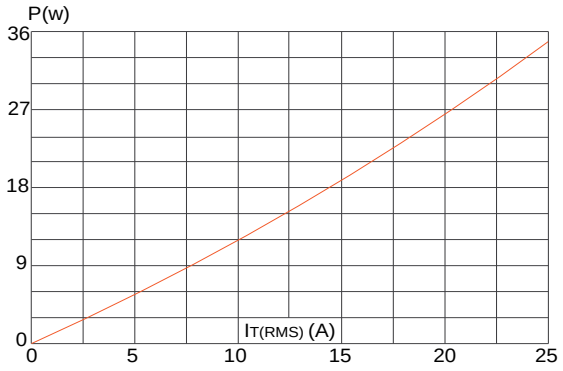


FIG2

RMS on-state current versus case temperature

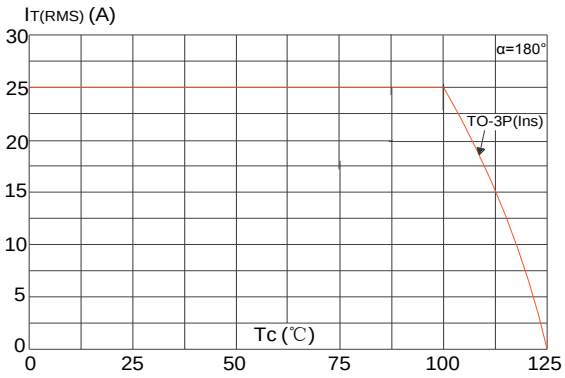


FIG3

Surge peak on-state current versus number of cycles

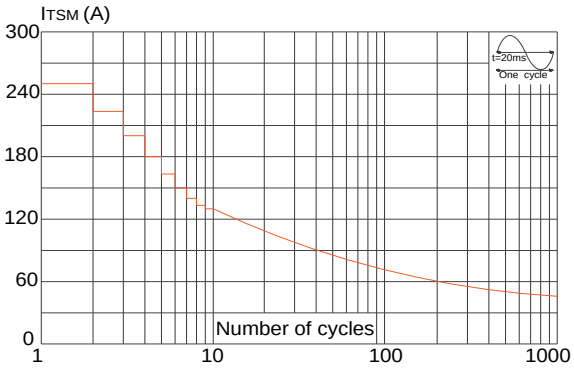


FIG4

On-state characteristics (maximum values)

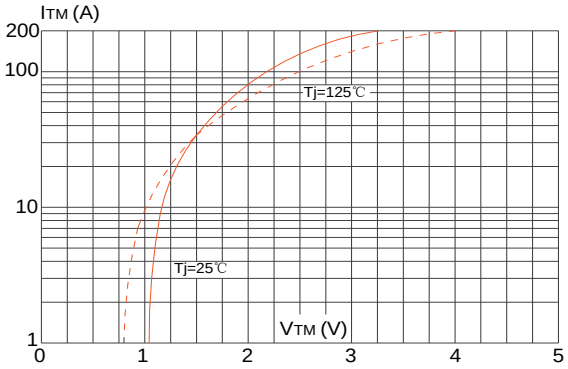


FIG5

Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t (dI/dt < 100A/μs)

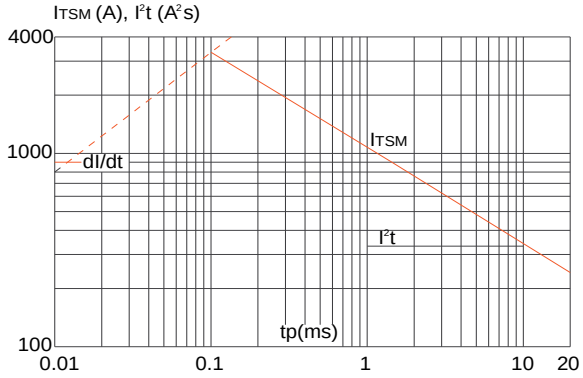
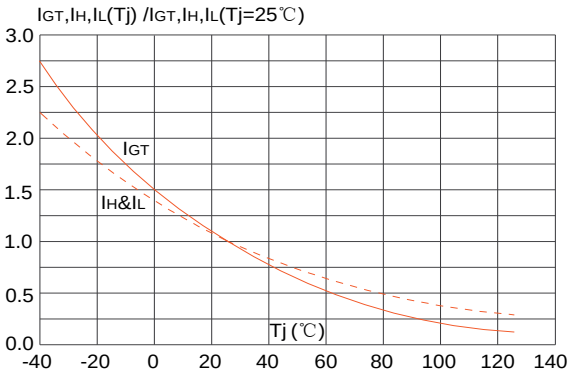


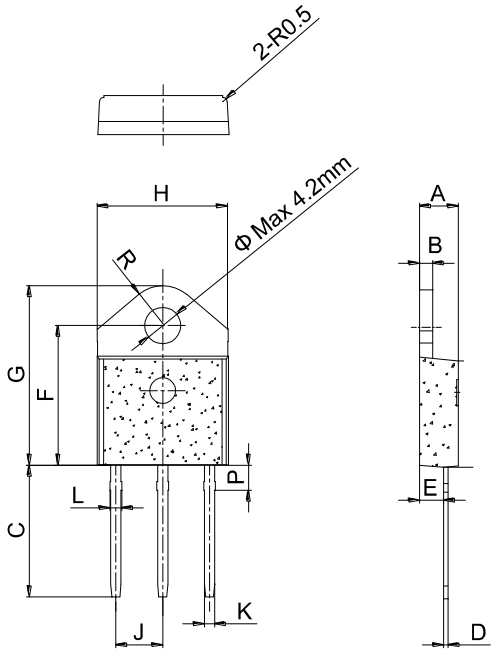
FIG6

FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature



Package Information

TO-3P



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	